

1 39. (New) A semiconductor laser according to Claim 1,
2 wherein the current-blocking layer is comprised of at least one of
3 AlInP and $(Al_xGa_{1-x})yIn_{1-y}P$, where $0.7 < x < 1$ and $y = 0.5$.

1 40. (New) A semiconductor laser according to Claim 12,
2 wherein the current-blocking layer is comprised of at least one of
3 AlInP and $(Al_xGa_{1-x})yIn_{1-y}P$, where $0.7 < x < 1$ and $y = 0.5$.

1 41. (New) A semiconductor laser according to Claim 25,
2 wherein the current-blocking layer is comprised of at least one of
3 AlInP and $(Al_xGa_{1-x})yIn_{1-y}P$, where $0.7 < x < 1$ and $y = 0.5$.

1 42. (New) A semiconductor laser according to Claim 35,
2 wherein the current-blocking layer is comprised of at least one of
3 AlInP and $(Al_xGa_{1-x})yIn_{1-y}P$, where $0.7 < x < 1$ and $y = 0.5$.

1 43. (New) A semiconductor laser according to Claim 36,
2 wherein the current-blocking layer is comprised of at least one of
3 AlInP and $(Al_xGa_{1-x})yIn_{1-y}P$, where $0.7 < x < 1$ and $y = 0.5$.